

A Gas-phase Electron Diffraction Study of Tris(trimethylsilyl)methane. A C–H Bond of High p-Character

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Summary The $\text{Me}_3\text{SiCSiMe}_3$ angles in $(\text{Me}_3\text{Si})_3\text{CH}$ are unusually large (117°), implying an unusually high degree of p-character in the orbital used to form the C–H bond.

SPECIAL interest attaches to compounds in which bond angles at a formally sp^3 -hybridized carbon atom are much larger than 109.5° (see, for example, ref. 1 and references therein). Examination of models suggested that the $\text{Me}_3\text{SiCSiMe}_3$ angles in $(\text{Me}_3\text{Si})_3\text{CH}$ could be expected to open up considerably to minimize steric strain. This should result in a high proportion of p-character in the unique C–H bond, and in agreement with this the value of $^1J(\text{CH})$ for this bond, 100 Hz ,² is unusually low. However, the hydrogen atom of this bond has a high acidity [the kinetic acidity of $(\text{Me}_3\text{Si})_3\text{CH}$ is higher than that of triphenylmethane³], a feature not normally associated with a bond of high p-character. It thus seemed of interest to determine the structure of $(\text{Me}_3\text{Si})_3\text{CH}$.

Gas-phase electron-diffraction patterns recorded photographically in the Balzers KDG2 instrument^{4–6} at UMIST were scanned microdensitometrically⁷ and the data obtained were processed by standard methods^{8–10} to molecular intensity curves suitable for least-squares refinement of the molecular structural parameters. Refinements employing the recently developed programme LSQ3¹¹ were based on a molecule with overall three-fold symmetry, local three-fold symmetry for the $-\text{CH}_3$ and $-\text{Si}(\text{CH}_3)_3$ groups, and vibrational amplitudes grouped according to distance type. Although all refinements led to similar bond lengths and angles, three least-squares minima were revealed, differing largely in the values of the two torsional angles τ_1 and τ_2

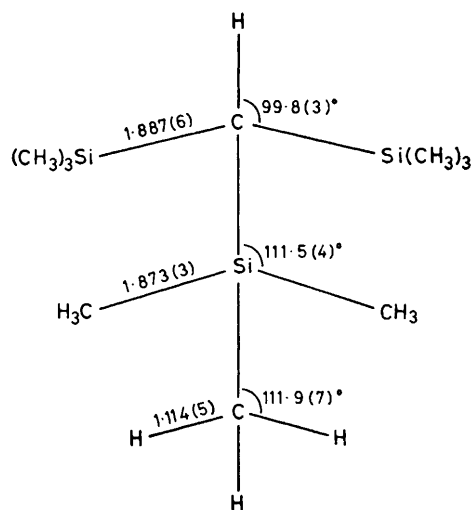


FIGURE 1. Bond lengths (Å) and angles ($^\circ$) in $(\text{Me}_3\text{Si})_3\text{CH}$ (e.s.d.s in parentheses).

(see Figure 2). The first two minima, which arose from different initial sets of parameters, were found to correspond with molecules possessing unreasonably short $\text{H} \cdots \text{H}$ and $\text{C} \cdots \text{H}$ distances. Molecular mechanics non-bonded interaction functions¹² for $\text{H} \cdots \text{H}$ and $\text{C} \cdots \text{H}$ contacts were employed to calculate the van der Waals potential energy for possible combinations of τ_1 and τ_2 values. The global energy minimum occurred at $\tau_1 82$ and $\tau_2 10^\circ$. A least-

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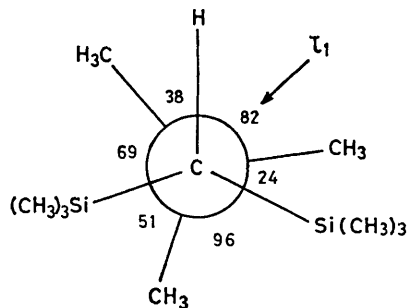


FIGURE 2. Newman projections down the C-SiMe₃ and Si-CH₃ bonds showing torsion angles (°).

squares refinement starting from this point led to the third minimum (having $\tau_1 = 81^\circ$, $\tau_2 = -18^\circ$) and produced better agreement between observed and calculated diffraction data than any of the previous refinements (Figure 3). Finally, the two distinct Si-C distances were allowed to refine independently, with the results shown in Figures 1 and 2 [$\tau_1 = 81.5(3)^\circ$ and $\tau_2 = -11(5)^\circ$]. The agreement with the observed data improved further, but hardly significantly. However, the torsional angles were then within *ca.* 4 e.s.d. of the calculated values.

As expected, the potential strain is mainly accommodated by distortion of bond angles, especially those at the central carbon atom, where $\angle \text{SiCSi} = 117.2(4)^\circ$ and $\angle \text{CHSi} = 99.8(3)^\circ$, but there is also considerable deviation of the torsional angles from the values typifying staggered conformations (Figure 2) and a slight lengthening of the Me₃Si-C (1.887 Å) compared with the CH₃-Si bonds (1.873 Å). There is a markedly greater lengthening of the Me₃C-C bonds in (Me₃C)₃CH, in which the Me₃CCCMe₃ angle is 116° .¹³

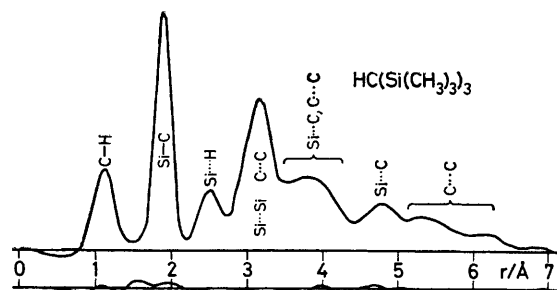


FIGURE 3. Observed and difference radial distribution curves (longer distances involving H not indicated).

The angles around the central carbon atom correspond to *s* and *p*¹³ character in the orbital used for the C-H bond. This contrasts with a value of *sp*⁴ which can be derived from the observed $^1J(\text{CH}) = 5 \times \% \text{ s-character}$, or the modified version¹⁴ $^1J(\text{CH}) = (5.7 \times \% \text{ s-character}) - 18.4$. (A value of 111.5° for $\angle \text{Me}_3\text{SiCSiMe}_3$ would be required for *sp*⁴ character in the C-H bond.) The electronic effect of the Me₃Si groups must have some influence on the coupling $^1J(\text{CH})$, but would be expected to favour an even lower value than would be implied by the geometry alone [compare the $^1J(\text{CH})$ values of 118 and 125 for Me₃Si and CH₄, respectively]. The apparent discrepancy might be related, at least in part, to the possibility that the inter-orbital angles in the Me₃SiCSiMe₃ linkages may be smaller than the internuclear angles,^{1,13} but it is also possible that the relationships mentioned above between $^1J(\text{CH})$ and *s*-character, which were derived by use of $^1J(\text{CH})$ values of 120 Hz or more, do not apply satisfactorily to substantially lower values. Detailed analysis is complicated by the report that the value of $^1J(\text{CH})$ for the corresponding bond in (Me₃C)₃CH is 124 Hz.¹³

The high acidity associated with a C-H bond of high *p*-character can be most simply attributed to delocalization of the lone pair of the conjugate carbanion into the *d*-orbitals of the silicon atoms, and the inherent effect may be substantially enhanced by the geometry of (Me₃Si)₃CH, since the near-planarity of the three silicon and central carbon atoms means that very little movement of atoms will be needed to give the maximum conjugative stabilization on going to the carbanion.

We thank S.R.C. for support.

(Received, 30th March 1981, Com. 351.)

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